

Silicon NPN Power Transistors

2SD2335

DESCRIPTION

www.datasheet4u.com

- With TO-3PFa package
- High voltage;high speed
- Built-in damper diode

APPLICATIONS

- For color TV horizontal output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

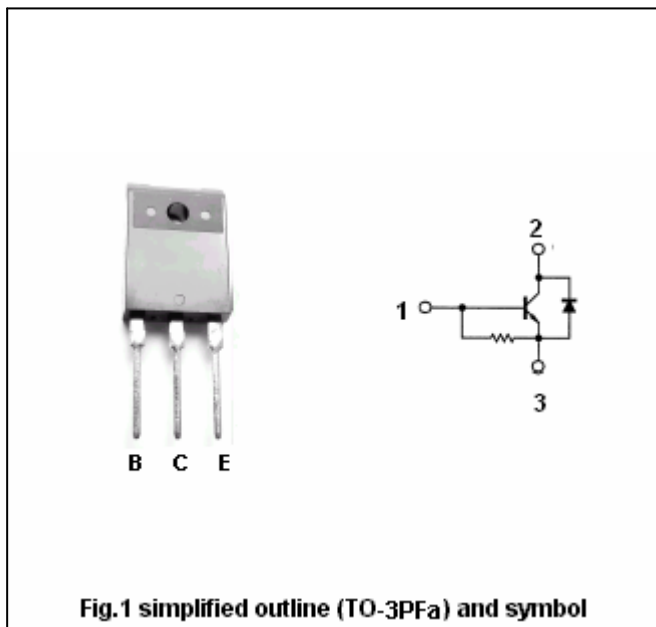


Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 600 | V |
| V _{EBO} | Emitter-base voltage | | 5 | V |
| I _C | Collector current | | 7 | A |
| I _B | Base current | | 1.5 | A |
| P _C | Collector power dissipation | T _C =25°C | 100 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

Silicon NPN Power Transistors

2SD2335

CHARACTERISTICS

T_j=25°C unless otherwise specified

www.datasheet4u.com

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA, I _B =0 | 600 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =200mA, I _C =0 | 5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =6A; I _B =1.2A | | | 5.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =6A; I _B =1.2A | | | 1.5 | V |
| I _{CB0} | Collector cut-off current | V _{CB} =800V I _E =0 | | | 10 | μA |
| h _{FE} | DC current gain | I _C =1A; V _{CE} =5V | 8 | | | |
| V _F | Diode forward voltage | I _F =6A | | | 2.0 | V |

